

RF Power FETs

N-Channel

Enhancement-Mode



175 MHz 20W
20-30V 10dB

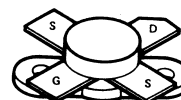
FEATURES

- Reduces Component Count and Design Time/Effort
- Withstands Infinite VSWR
- High Gain
- High Two-Tone Intermodulation Intercept Point
- Low Small Signal Noise Figure
- Linear Transfer Characteristics
- Permits Broadband Designs
- High Input Impedance
- Low Noise Figure
- Permits Efficient Switching Amplifier Designs
- High Input Impedance
- No Storage Delay Time
- Improves Reliability
- Free From Secondary Breakdown Failures and Voltage Derating
- Output Current Decreases as Temperature Increases

APPLICATIONS

- VHF Broadband Amplifiers
- Receiver Front Ends
- Class A, B, C, D, E Amplifiers
- Power Oscillators

S - Package



380 SOE
FLANGE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

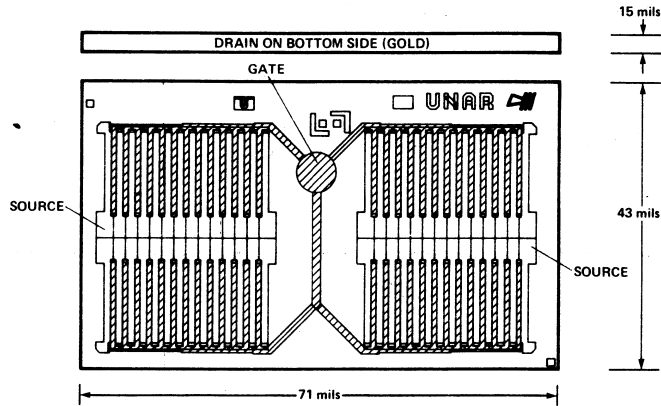
Gate-Source Voltage	30 V	Total Device Dissipation	25 W
Drain-Source Voltage	60 V	Thermal Resistance, Junction to Case	7°C/W
Drain-Gate Voltage	60 V	Junction Temperature	200°C
Drain Current (DC)	2.0 A	Storage Temperature Range	-55 to 150°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	60			V	$V_{GS} = 0V, I_D = 1.0 \text{ mA}$
I_{DSS}	Drain-Source Leakage Current			100	μA	$V_{GS} = 0V, V_{DS} = 25V$
I_{GSS}	Gate-Source Leakage Current			100	nA	$V_{GS} = 30V, V_{DS} = 0V$
g_m	D. C. Forward Transconductance	170	240		mS	$V_{DS} = 25V, I_D = 0.5A, \Delta V_{GS} = 1.0V$
$I_D(\text{on})$	On-State Drain Current	400			mA	$V_{DS} = 25V, V_{GS} = 5V$
$V_{GS(th)}$	Gate Threshold Voltage		2.4		V	$V_{GS} = V_{DS}, I_D = 100 \text{ mA}$
C_{iss}	Common-Source Input Capacitance		32		pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0 \text{ MHz}$
C_{oss}	Common-Source Output Capacitance		34		pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0 \text{ MHz}$
C_{rss}	Reverse Transfer Capacitance		4.8		pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0 \text{ MHz}$
G_{ps}	Common Source Power Gain	10			dB	$V_{DD} = 28V, P_o = 20W, f = 175 \text{ MHz}$ $I_{DQ} = 100 \text{ mA}$
η	Drain Efficiency		65		%	$V_{DD} = 28V, P_o = 20W, f = 175 \text{ MHz}$ $I_{DQ} = 100 \text{ mA}$
V_{SWR}	Load Mismatch Tolerance	30:1				$V_{DD} = 28V, P_o = 20W, f = 175 \text{ MHz}$ $I_{DQ} = 100 \text{ mA}$
N. F.	Noise Figure		2.5		dB	$V_{DS} = 24V, I_D = 100 \text{ mA}, f = 150 \text{ MHz}$

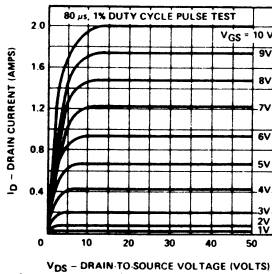
VNAR-RF

VMP4 PERFORMANCE CHARACTERISTICS (Cont'd)

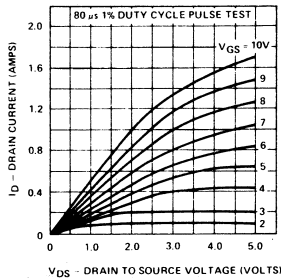


TYPICAL PERFORMANCE CURVES (25°C unless otherwise noted)

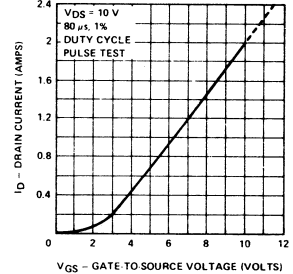
Output Characteristics



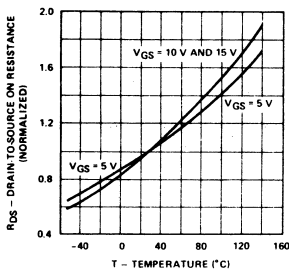
Saturation Characteristics



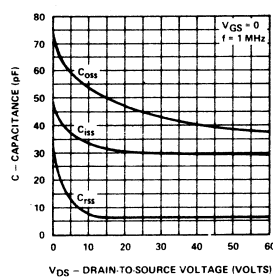
Static Transfer Characteristic



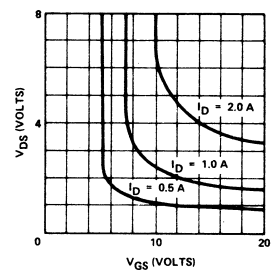
Normalized Drain-to-Source ON Resistance vs Temperature



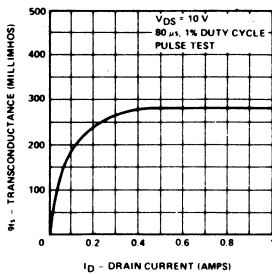
Capacitance vs Drain-to-Source Voltage



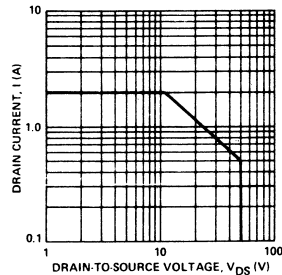
Saturated Drain-Source Voltage vs Gate-Source Voltage



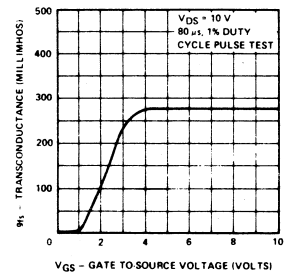
Transconductance vs Drain Current



DC Safe Operating Area



Transconductance vs Gate-to-Source Voltage

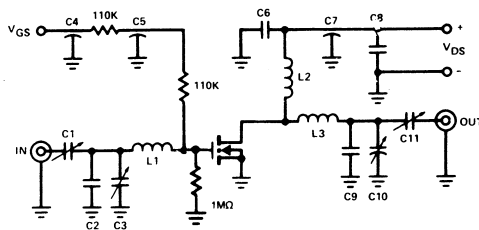


VMP4 PERFORMANCE CHARACTERISTICS (Cont'd)

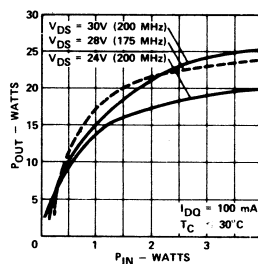
- C1 Arco 422 4-40 pf
 C2 100 pf
 C3 Arco 422 4-40 pf
 C4 .001 μ f
 C5 .001 μ f
 C6 .1 μ f Disk
 C7 .001 μ f
 C8 .1 μ f Disk
 C9 8.2 pf
 C10 Arco 402 1.5-20 pf
 C11 Arco 422 4-40 pf

- L1 2" Length #12 AWG
 L2 6 Turns #18 AWG .4 Inner dia. close wound
 L3 2" Length #12 AWG

VMP4 175 MHz Test Fixture

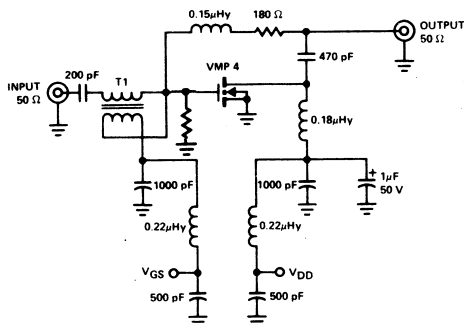


Typical Output Power vs Input Power

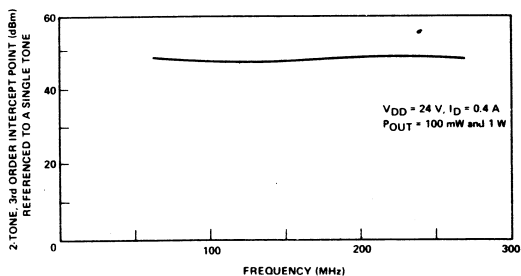


APPLICATIONS

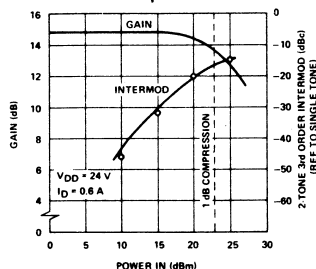
Broadband Amplifier



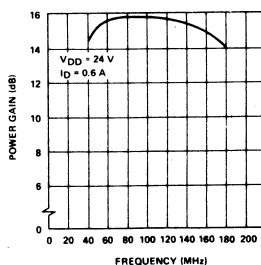
Broadband Amplifier Performance



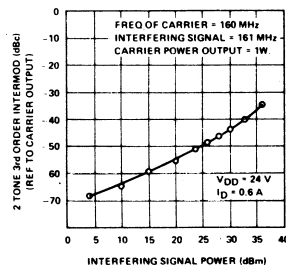
Gain and 2-Tone 3rd Order Intermodulation Broadband Amplifier



Broadband Amplifier



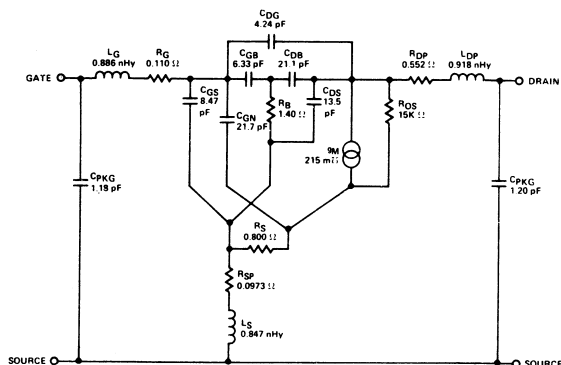
Effects of Interference



VMP4 PERFORMANCE CHARACTERISTICS



VMP4 Equivalent Circuit

SMALL-SIGNAL POLAR S-PARAMETERS IN
50.0 OHM SYSTEM

FREQ MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂		S ₂₁ dB
	(MAGN)	(ANGL)	(MAGN)	(ANGL)	(MAGN)	(ANGL)	(MAGN)	(ANGL)	
1.00	1.00	-3	20.98	177.7	-50dB	87.8	0.99	-3	26.43
2.00	1.00	-6	20.94	175.5	0.005	85.6	0.99	-6	26.42
5.00	0.99	-15	20.67	168.7	0.013	79.3	0.98	-15	26.31
10.00	0.96	-29	19.79	158.0	0.025	69.0	0.96	-29	25.93
20.00	0.89	-53	17.13	139.6	0.043	51.6	0.88	-54	24.68
50.00	0.73	-98	10.19	106.4	0.063	21.5	0.73	-99	20.16
100.00	0.70	-126	5.31	80.4	0.061	1.4	0.70	-128	14.50
120.00	0.71	-132	4.33	73.4	0.057	-2.8	0.71	-134	12.73
160.00	0.75	-140	3.06	62.2	0.047	-6.7	0.74	-142	9.70
200.00	0.78	-147	2.27	53.5	0.037	-4.5	0.78	-149	7.13
220.00	0.80	-150	1.99	49.8	0.032	0.5	0.79	-151	5.96
260.00	0.83	-154	1.56	43.6	0.026	15.3	0.82	-156	3.84
300.00	0.85	-158	1.25	38.6	0.025	38.8	0.84	-160	1.94
320.00	0.86	-160	1.13	36.5	0.026	49.8	0.85	-162	1.06
360.00	0.88	-164	0.94	33.0	0.033	65.3	0.86	-165	-0.57
400.00	0.89	-167	0.79	30.3	0.042	73.6	0.88	-168	-2.04

SMALL-SIGNAL TWO-PORT Y-PARAMETER
MATRIX IN MILLIMHOS

FREQ MHz	Y ₁₁		Y ₂₁		Y ₁₂		Y ₂₂	
	(REAL)	(IMAG)	(REAL)	(IMAG)	(REAL)	(IMAG)	(REAL)	(IMAG)
1.0	0.00	0.24	210.58	-0.30	0.00	-0.03	0.07	0.25
2.0	-0.00	0.48	210.58	-0.61	0.00	-0.05	0.07	0.50
5.0	0.00	1.20	210.59	-1.52	0.00	-0.13	0.07	1.24
10.0	0.02	2.39	210.64	-3.05	0.00	-0.27	0.09	2.48
20.0	0.09	4.78	210.84	-6.11	0.00	-0.53	0.17	4.95
50.0	0.56	11.97	212.25	-15.47	0.02	-1.31	0.74	12.41
100.0	2.32	24.09	217.24	-32.49	0.11	-2.50	2.88	24.95
120.0	3.42	29.00	220.13	-40.12	0.18	-2.91	4.21	30.01
160.0	6.42	38.92	227.33	-57.56	0.43	-3.57	7.85	40.21
200.0	10.75	48.88	236.01	-79.01	0.94	-3.93	13.07	50.36
220.0	13.52	53.79	240.62	-91.74	1.36	-3.98	16.39	55.30
260.0	20.45	63.15	249.36	-122.30	2.69	-3.76	24.69	64.52
300.0	29.40	71.16	255.01	-160.94	5.06	-3.17	35.35	71.95
320.0	34.56	74.76	255.36	-183.50	6.81	-2.81	41.48	74.57
360.0	45.63	77.74	247.61	-234.10	11.81	-2.31	54.55	76.29
400.0	55.76	76.70	224.34	-287.36	19.10	-2.93	66.44	72.51